

### **INCHANGE SEMICONDUCTOR**

## **isc Silicon NPN Power Transistor**

# BD135

### DESCRIPTION

- DC Current Gain-
  - : h<sub>FE</sub>= 40(Min)@ I<sub>C</sub>= 0.15A
- · Collector-Emitter Sustaining Voltage -

: V<sub>CEO(SUS)</sub>= 45V(Min)

- Complement to type BD136
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

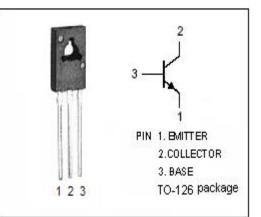
• Designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

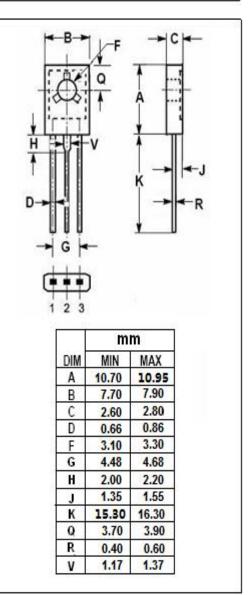
ABSOLUTE MAXIMUM KATINGS(Ta=25 C)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	45	v				
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V				
V <sub>EBO</sub>	Emitter-Base Voltage	5	V				
lc	Collector Current-Continuous	1.5	A				
I <sub>B</sub>	Base Current-Continuous 0.5		A				
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.25	w				
	Collector Power Dissipation @ $T_c=25^{\circ}C$	12.5					
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C				

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	10	°C/W	
Rth j-a	Thermal Resistance, Junction to Ambient	100	°C/W	





isc website: <u>www.iscsemi.com</u>



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### ELECTRICAL CHARACTERISTICS

#### $T_{\text{C}}\text{=}25\,^\circ\!\!\!\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	ΜΙΝ	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA ; I <sub>B</sub> =0	45			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA			0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 2V			1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>E</sub> = 0 V <sub>CB</sub> = 30V; I <sub>E</sub> = 0,T <sub>C</sub> =125℃			0.1 10	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			10	μ Α
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 2V	25			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 2V	25			
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 0.15A ; V <sub>CE</sub> = 2V	40		250	

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